

**75A, 55V, 0.009 Ohm, N-Channel UltraFET
Power MOSFETs**



These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology achieves the lowest possible on-

resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery operated products.

Formerly developmental type TA75343.

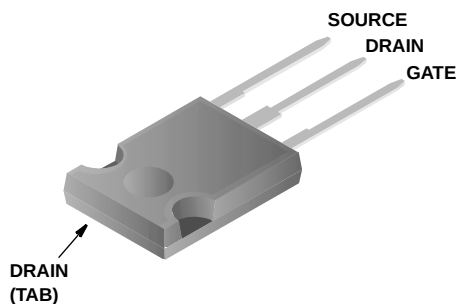
Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75343G3	TO-247	75343G
HUF75343P3	TO-220AB	75343P
HUF75343S3	TO-262AA	75343S
HUF75343S3S	TO-263AB	75343S

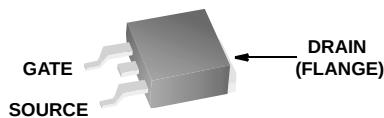
NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUF75343S3ST.

Packaging

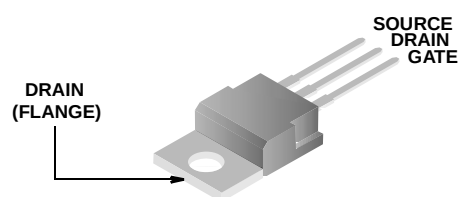
JEDEC STYLE TO-247



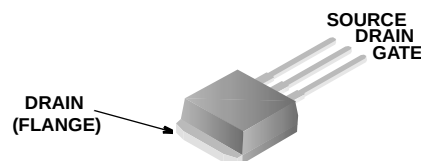
JEDEC TO-263AB



JEDEC TO-220AB



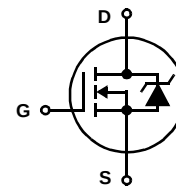
JEDEC TO-262AA



Features

- 75A, 55V
- Simulation Models
 - Temperature Compensating PSPICE® and SABER™ Models
 - Thermal Impedance PSPICE™ and SABER Models Available on the WEB at: www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Product reliability information can be found at <http://www.fairchildsemi.com/products/discrete/reliability/index.html>

For severe environments, see our Automotive HUFA series.

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HUF75343G3, HUF75343P3, HUF75343S3, HUF75343S3S

Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

		UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	55 V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR}	55 V
Gate to Source Voltage	V_{GS}	± 20 V
Drain Current		
Continuous (Figure 2)	I_D	75 A
Pulsed Drain Current	I_{DM}	Figure 4
Pulsed Avalanche Rating	E_{AS}	Figure 6
Power Dissipation	P_D	270 W
Derate Above 25°C		1.81 $\text{W}/^{\circ}\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 175 $^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.	T_L	300 $^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260 $^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 11)	55	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 50V, V _{GS} = 0V	-	-	1	μA	
		V _{DS} = 45V, V _{GS} = 0V, T _C = 150 ⁰ C	-	-	250	μA	
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V	-	-	±100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA (Figure 10)	2	-	4	V	
Drain to Source On Resistance	r _{DS(ON)}	I _D = 75A, V _{GS} = 10V (Figure 9)	-	0.007	0.009	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	R _{θJC}	(Figure 3)	-	-	0.55	°C/W	
Thermal Resistance Junction to Ambient	R _{θJA}	TO-247	-	-	30	°C/W	
		TO-220, TO-263	-	-	62	°C/W	
SWITCHING SPECIFICATIONS (V _{GS} = 10V)							
Turn-On Time	t _{ON}	V _{DD} = 30V, I _D ≅ 75A, R _L = 0.4Ω, V _{GS} = 10V, R _{GS} = 2.5Ω	-	-	125	ns	
Turn-On Delay Time	t _{d(ON)}		-	9	-	ns	
Rise Time	t _r		-	75	-	ns	
Turn-Off Delay Time	t _{d(OFF)}		-	32	-	ns	
Fall Time	t _f		-	18	-	ns	
Turn-Off Time	t _{OFF}		-	-	75	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 20V	V _{DD} = 30V, I _D ≅ 75A, R _L = 0.4Ω I _{g(REF)} = 1.0mA (Figure 13)	-	170	205	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V		-	92	110	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V		-	6.0	7.2	nC
Gate to Source Gate Charge	Q _{gs}			-	13	-	nC
Gate to Drain “Miller” Charge	Q _{gd}			-	42	-	nC

HUF75343G3, HUF75343P3, HUF75343S3, HUF75343S3S

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 12)	-	3000	-	pF
Output Capacitance	C_{OSS}		-	1100	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	230	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 75\text{A}$	-	-	1.25	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 75\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 75\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	200	nC

Typical Performance Curves

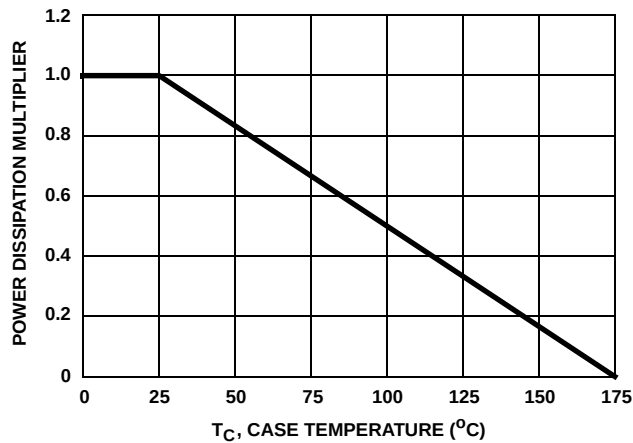


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

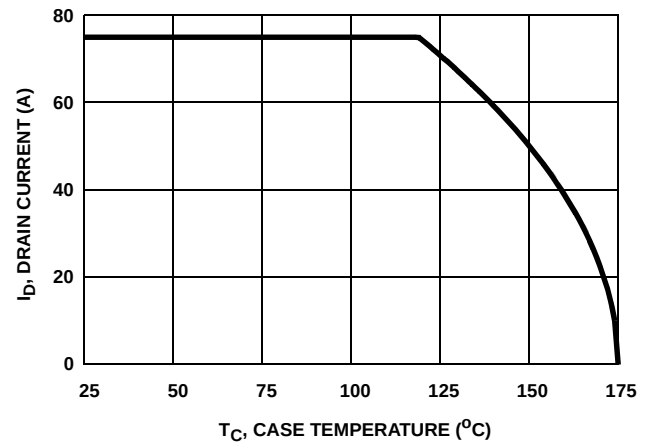


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

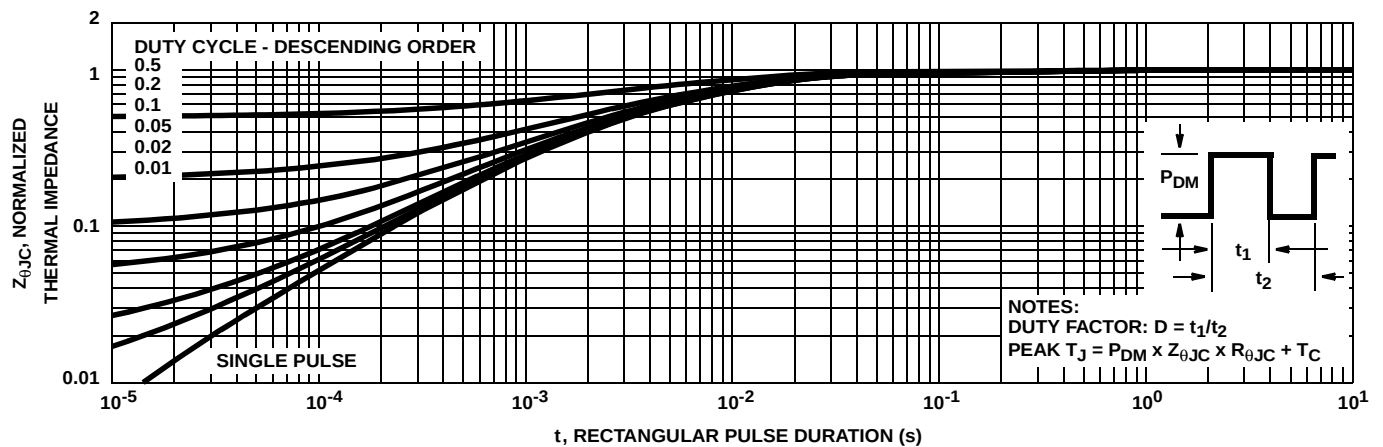


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves (Continued)

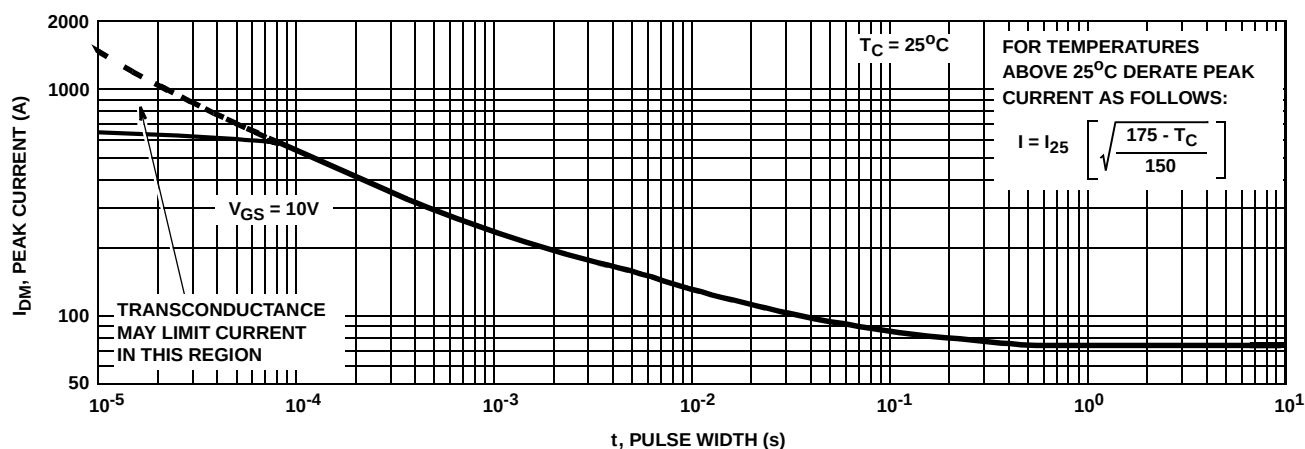


FIGURE 4. PEAK CURRENT CAPABILITY

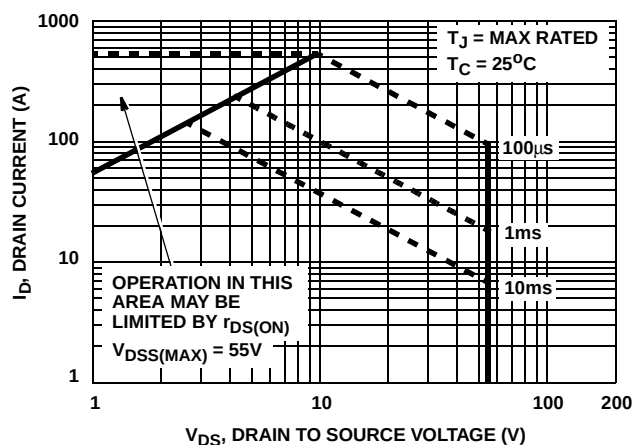
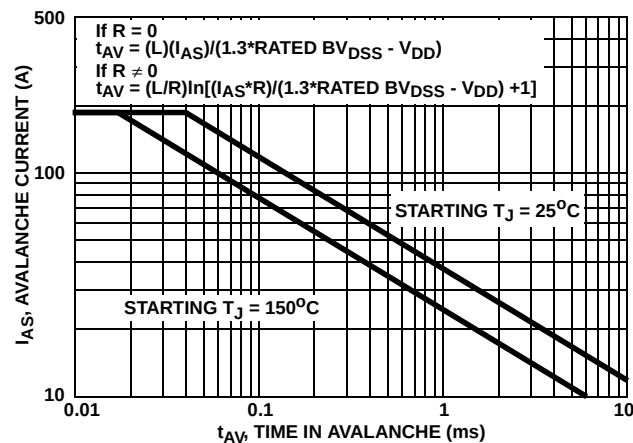


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

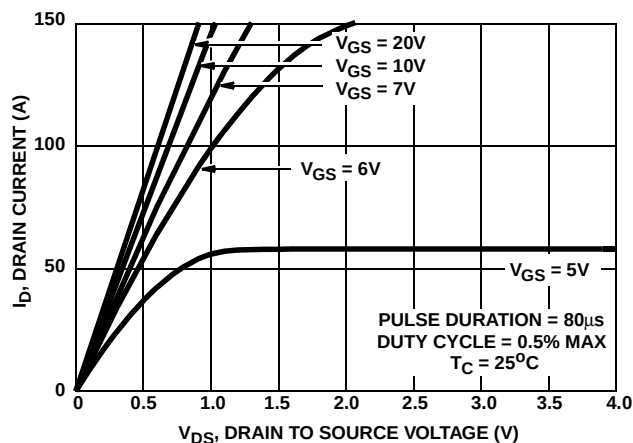


FIGURE 7. SATURATION CHARACTERISTICS

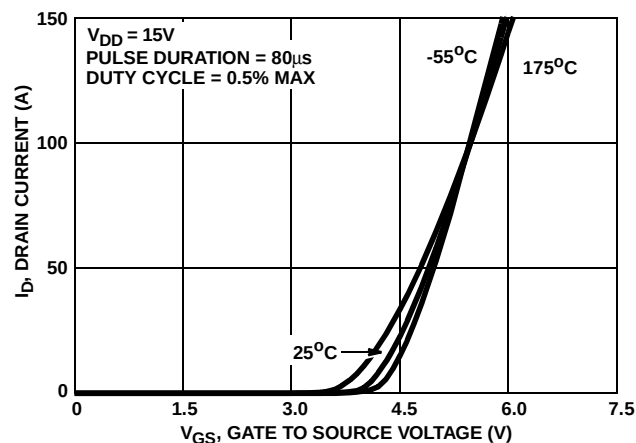


FIGURE 8. TRANSFER CHARACTERISTICS

Typical Performance Curves (Continued)

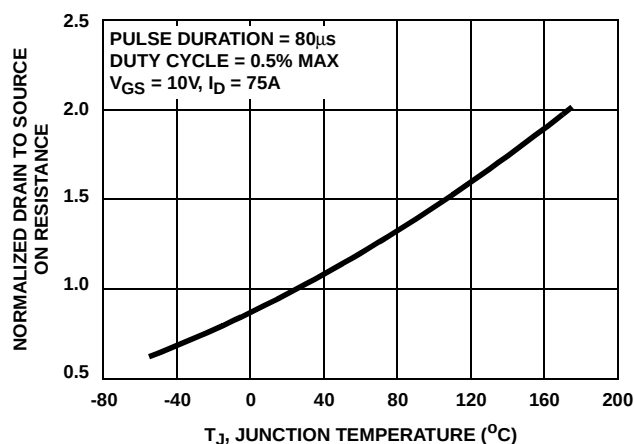


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

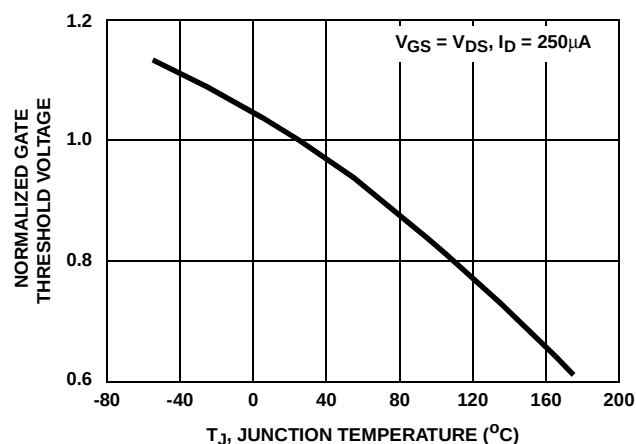


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

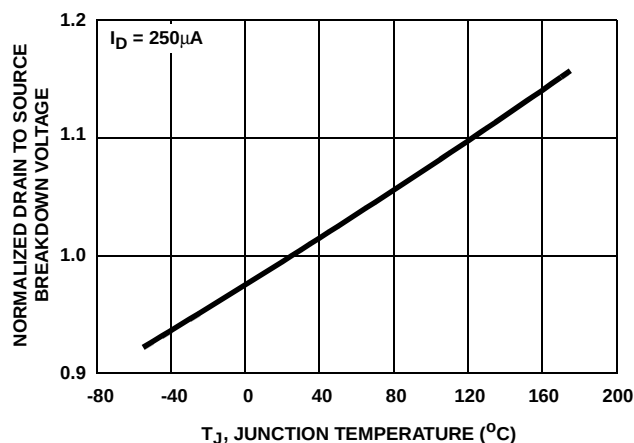


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

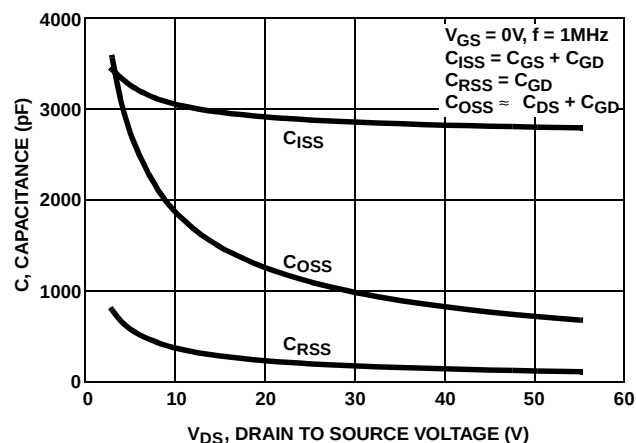
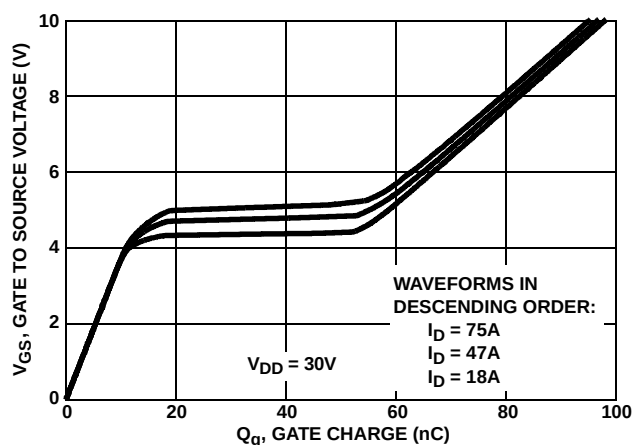


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

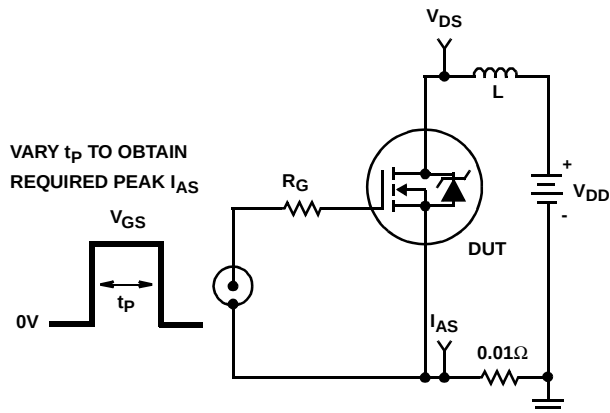


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

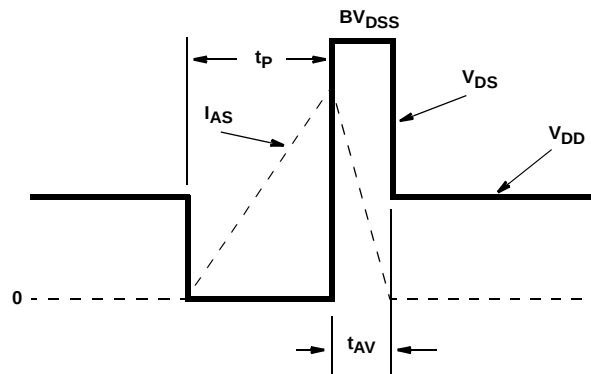


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

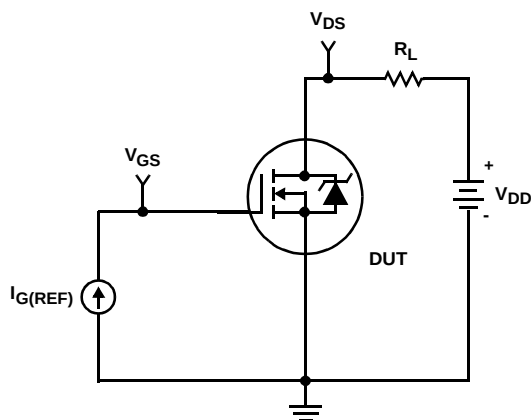


FIGURE 16. GATE CHARGE TEST CIRCUIT

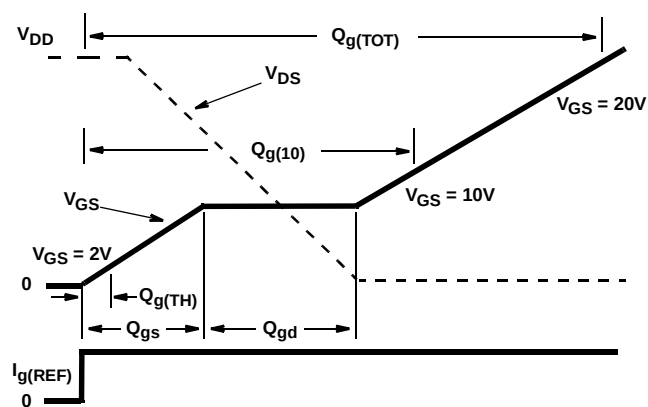


FIGURE 17. GATE CHARGE WAVEFORM

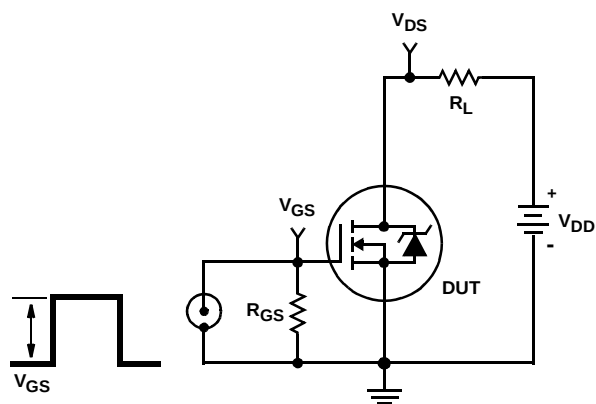


FIGURE 18. SWITCHING TIME TEST CIRCUIT

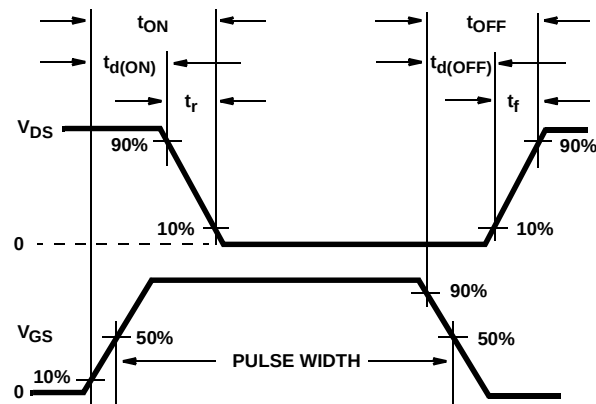


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

SPICE Thermal Model

REV 12 February 1999

HUF75343

CTHERM1 th 6 6.15e-3
 CHERM2 6 5 2.50e-2
 CHERM3 5 4 1.40e-2
 CHERM4 4 3 1.25e-2
 CHERM5 3 2 4.85e-2
 CHERM6 2 tl 12.55

RHERM1 th 6 3.76e-3
 RHERM2 6 5 9.35e-3
 RHERM3 5 4 2.64e-2
 RHERM4 4 3 1.48e-1
 RHERM5 3 2 2.23e-1
 RHERM6 2 tl 2.96e-2

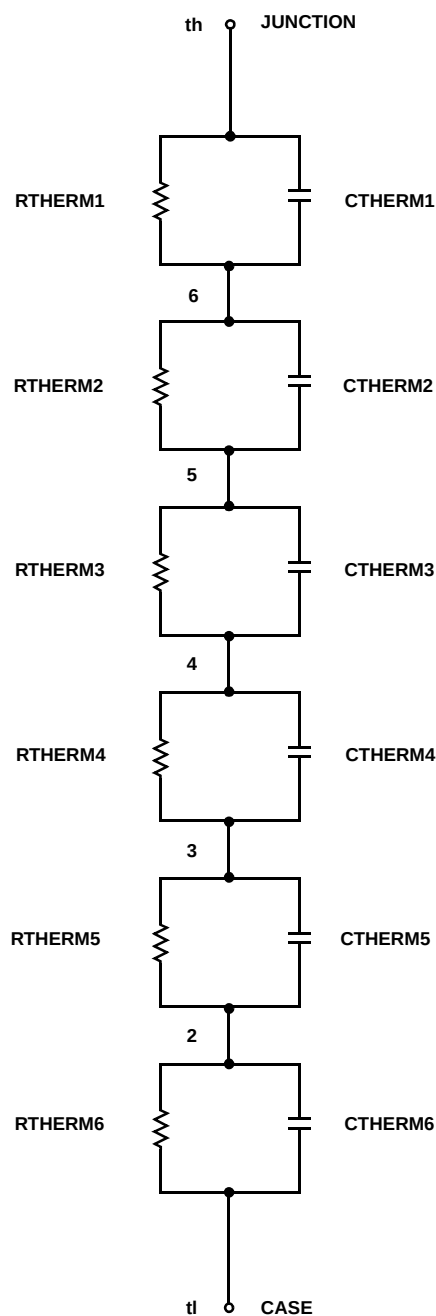
SABER Thermal Model

SABER thermal model HUF75343

```
template thermal_model th tl
thermal_c th, tl
{
    ctherm.therm1 th 6 = 6.15e-3
    ctherm.therm2 6 5 = 2.50e-2
    ctherm.therm3 5 4 = 1.40e-2
    ctherm.therm4 4 3 = 1.25e-2
    ctherm.therm5 3 2 = 4.85e-2
    ctherm.therm6 2 tl = 12.55
```

```

rtherm.rtherm1 th 6 = 3.76e-3
rtherm.rtherm2 6 5 = 9.35e-3
rtherm.rtherm3 5 4 = 2.64e-2
rtherm.rtherm4 4 3 = 1.48e-1
rtherm.rtherm5 3 2 = 2.23e-1
rtherm.rtherm6 2 tl = 2.96e-2
}
```



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CoolFET [™]	FAST ^r [™]	MicroFET [™]	PowerTrench [®]	SuperSOT [™] -6
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PRODUCT STATUS DEFINITIONS

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